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## JP2241014A2: SOLID ELECTROLYTIC CAPACITOR

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Country: **JP Japan**

Kind:

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Application Number: **JP1989000062923**

IPC Class: **H01G 9/02;**

Abstract: **Purpose:** To obtain a device of high performance and reliability in which new organic semiconductor having small resistivity and thermal stability is used as solid-state electrolyte, by using specified bis(amidinohydrazone) dielectric TCNQ salt as the solid electrolyte. **Constitution:** As electrolyte, bis(amidinohydrazone) dielectric 7,7,8,8- tetracyanoquimodimethane slat shown by a formula 1 is used. R in the formula represents diacetyl, p-quinon or terephthalaldehyd. For example, diacetyl-bis(amidinohydrazone) TCNQ salt is dissolved in acetonitrile, and saturated solution is obtained; after a capacitance element is dipped in the solution, vacuum drying is performed at 50-60°C, thereby dispersing acetonitrile as the solvent; the above operation is repeated three times. An aluminum foil whose surface is etched at about ten times is used as the electrode of a capacitor element, and further the surface is subjected to formation treatment, thereby forming an oxide film.

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Other Abstract Info: **DERABS C90-332721 DERC90-332721**

Foreign References: **(No patents reference this one)**

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